

What is claimed is:

1. A method for producing an SOI wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer and a bond wafer having a micro bubble layer formed by gas ion implantation and a step of delaminating a wafer having an SOI layer at the micro bubble layer as a border, wherein a CZ wafer produced from a single crystal ingot of which COPs are reduced for the whole crystal is used as the bond wafer.

2. The method for producing an SOI wafer according to Claim 1, wherein the wafer having an SOI layer is subjected to a heat treatment under an atmosphere containing hydrogen or argon in a batch processing type furnace after the delamination step.

3. An SOI wafer produced by the method according to Claim 2, which has an RMS value of 0.5 nm or less concerning surface roughness for both of 1 μm square and 10 μm square.